SN74AHC1G32 シングル 2 入力、正論理 OR ゲート

1 特長

- 動作範囲:2V～5.5V
- 最大 t_{pd} 6.5ns (5V 時)
- 低消費電力、最大 I_{CC}:10µA
- 5V で ±8mA の出力駆動能力
- 全入力でのシュミット トリガ アクションにより、低速の入力立ち上がり / 立ち下がり時間を許容
- JESD 17 準拠で 250mA 超のラッチアップ性能

2 アプリケーション

- AV レシーバ
- 携帯用オーディオ ドック
- Blu-ray プレーヤおよびホーム シアター
- MP3 プレーヤ / レコーダ
- パーソナル デジタル アシスタント(PDA)
- 電源:
  - テレコム / サーバー AC/DC 電源
  - シングル コントローラ
    - アナログ
    - デジタル
- クライアントおよびエンタープライズ SSD (ソリッド ステート ドライブ)
- LCD およびデジタル TV、高解像度 TV (HDTV)
- エンタープライズ タブレット
- ビデオ アナリティクス サーバー
- ワイヤレス ヘッドセット、キーボード、マウス

3 概要

SN74AHC1G32 はシングル 2 入力正論理 OR ゲートです。このデバイスはブール関数 $Y = A + B$ or $Y = \overline{A \cdot B}$ を正論理で実行します。

パッケージ情報

部品番号	パッケージ (1)	パッケージ サイズ(2)	本体サイズ (3)
SN74AHC1G32	DBV (SOT-23、5)	2.90mm × 2.8mm	2.90mm × 1.60mm
	DCK (SC70、5)	2.00mm × 2.1mm	2.00mm × 1.25mm
	DRL (SOT、5)	1.60mm × 1.6mm	1.60mm × 1.20mm

(1) 詳細については、セクション 11 を参照してください。
(2) パッケージ サイズ (長さ × 幅) は公称値であり、該当する場合はピンも含まれます。
(3) 本体サイズ (長さ×幅) は公称値であり、ピンは含まれません。

概略回路図

このリソースの元の言語は英語です。翻訳は概要を便宜的に提供するもので、自動化ツール (機械翻訳) を使用していることがあり、TI では翻訳の正確性および妥当性につきましては一切保証いたしません。実際の設計などの前には、ti.com で必ず最新の英語版をご参照くださいますようお願いいたします。

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4 Pin Configuration and Functions

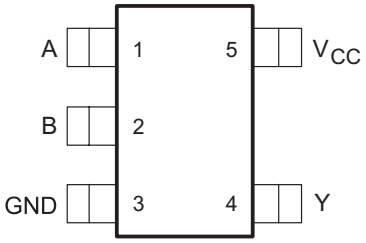


図 4-1. DBV Package 5-Pin SOT-23 Top View

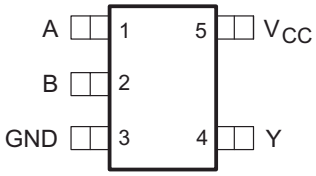
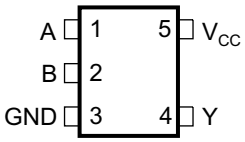


図 4-2. DCK Package 5-Pin SC70 Top View



See mechanical drawings for dimensions.

図 4-3. DRL Package 5-Pin SOT Top View

表 4-1. Pin Functions

PIN		TYPE(1)	DESCRIPTION
NO.	NAME		
1	A	I	Input A
2	B	I	Input B
3	GND	—	Ground Pin
4	Y	O	Output Y
5	V_{CC}	—	Power Pin

(1) Signal Types: I = Input, O = Output, I/O = Input or Output

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5 Specifications

5.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted) (1)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		–0.5	7	V
V_I	Input voltage (2)		–0.5	7	V
V_O	Output voltage (2)		–0.5	V_{CC} + 0.5	V
I_{IK}	Input clamp current	(V_I < 0)		–20	mA
I_{OK}	Output clamp current	(V_O < 0 or V_O > V_{CC})		±20	mA
I_O	Continuous output current	(V_O = 0 to V_{CC})		±25	mA
	Continuous current through V_{CC} or GND			±50	mA
T_J	Maximum junction temperature			150	°C
T_{stg}	Storage temperature		–60	150	°C

(1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions* is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
(2) The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

5.2 ESD Ratings

			VALUE	UNIT
$V_{(ESD)}$	Electrostatic discharge	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001(1)	±1500	V
		Charged device model (CDM), per JEDEC specification JESD22-C101(2)	±1000	

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

5.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)(1)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		2	5.5	V
V_{IH}	High-level input voltage	V_{CC} = 2 V	1.5		V
		V_{CC} = 3 V	2.1		
		V_{CC} = 5.5 V	3.85		
V_{IL}	Low-level input voltage	V_{CC} = 2 V		0.5	V
		V_{CC} = 3 V		0.9	
		V_{CC} = 5.5 V		1.65	
V_I	Input voltage		0	5.5	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2 V		–50	µA
		V_{CC} = 3.3 V ± 0.3 V		–4	mA
		V_{CC} = 5 V ± 0.5 V		–8	
I_{OL}	Low-level output current	V_{CC} = 2 V		50	µA
		V_{CC} = 3.3 V ± 0.3 V		4	mA
		V_{CC} = 5 V ± 0.5 V		8	
$\Delta t/\Delta v$	Input transition rise and fall rate	V_{CC} = 3.3 V ± 0.3 V		100	ns/V
		V_{CC} = 5 V ± 0.5 V		20	

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over operating free-air temperature range (unless otherwise noted)(1)

		MIN	MAX	UNIT
T_A	Operating free-air temperature	–40	125	°C

(1) All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. See *Implications of Slow or Floating CMOS Inputs*, SCBA004.

5.4 Thermal Information

THERMAL METRIC(1)		SN74AHC1G32			UNIT
		DBV (SOT-23)	DCK (SC70)	DRL (SOT)	
		5 PINS	5 PINS	5 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	278	293.4	328.7	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	180.5	208.8	105.1	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	184.4	180.6	150.3	°C/W
ψ_{JT}	Junction-to-top characterization parameter	115.4	120.6	6.9	°C/W
ψ_{JB}	Junction-to-board characterization parameter	183.4	179.5	148.4	°C/W
$R_{\theta JC(bot)}$	Junction-to-case (bottom) thermal resistance	N/A	N/A	N/A	°C/W

(1) For more information about traditional and new thermal metrics, see the *Semiconductor and IC Package Thermal Metrics* application report.

5.5 Electrical Characteristics

over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		V_{CC}	T_A = 25°C			–40 TO +80°C		–40 TO +125°C		UNIT
					MIN	TYP	MAX	MIN	MAX	MIN	MAX	
V_{OH}	High level output voltage	I_{OH} = –50 µA		2 V	1.9	2		1.9		1.9		V
				3 V	2.9	3		2.9		2.9		
				4.5 V	4.4	4.5		4.4		4.4		
		I_{OH} = –4 mA		3 V	2.58			2.48		2.48		
		I_{OH} = –8 mA		4.5 V	3.94			3.8		3.8		
V_{OL}	Low level output voltage	I_{OL} = 50 µA		2 V			0.1		0.1		0.1	v
				3 V			0.1		0.1		0.1	
				4.5 V			0.1		0.1		0.1	
		I_{OL} = 4 mA		3 V			0.36		0.44		0.44	
		I_{OL} = 8 mA		4.5 V			0.36		0.44		0.44	
I_I	Input leakage current	V_I = 5.5 V or GND		0 V to 5.5 V			±0.1		±1		±1	µA
I_{CC}	Supply current	V_I = V_{CC} or GND,	I_O = 0	5.5 V			1		10		10	µA
C_i	Input Capacitance	V_I = V_{CC} or GND		5 V		2	10		10		10	pF

5.6 Switching Characteristics, V_{CC} = 3.3 V ± 0.3 V

over recommended operating free-air temperature range (unless otherwise noted) (see Load Circuit And Voltage Waveforms)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	LOAD CAPACITANCE	T_A = 25°C			–40°C to +85°C			–40°C to +125°C			UNIT
				MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	
t_{PLH}	A or B	Y	C_L = 15 pF		5.5	7.9	1		9.5	1		10	ns
t_{PHL}					5.5	7.9	1		9.5	1		10	

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over recommended operating free-air temperature range (unless otherwise noted) (see Load Circuit And Voltage Waveforms)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	LOAD CAPACITANCE	T_A = 25°C			–40°C to +85°C			–40°C to +125°C			UNIT
				MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	
t_{PLH}	A or B	Y	C_L = 50 pF		8	11.4	1		13	1		14	ns
t_{PHL}					8	11.4	1		13	1		14	

5.7 Switching Characteristics, V_{CC} = 5 V ± 0.5 V

over recommended operating free-air temperature range (unless otherwise noted) (see Load Circuit And Voltage Waveforms)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	LOAD CAPACITANCE	T_A = 25°C			–40°C to +85°C			–40°C to +125°C			UNIT
				MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	
t_{PLH}	A or B	Y	C_L = 15 pF		3.8	5.5	1		6.5	1		7	ns
t_{PHL}					3.8	5.5	1		6.5	1		7	
t_{PLH}	A or B	Y	C_L = 50 pF		5.3	7.5	1		8.5	1		9.5	ns
t_{PHL}					5.3	7.5	1		8.5	1		9.5	

5.8 Operating Characteristics

V_{CC} = 5 V, T_A = 25°C

PARAMETER		TEST CONDITIONS		TYP	UNIT
C_{pd}	Power dissipation capacitance	No load,	f = 1 MHz	14	pF

5.9 Typical Characteristics

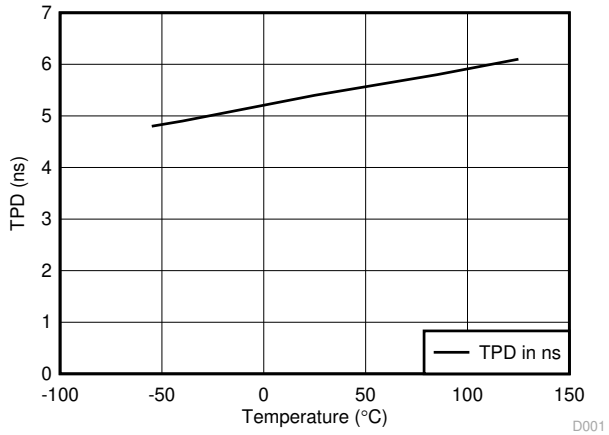

図 5-1. TPD vs Temperature

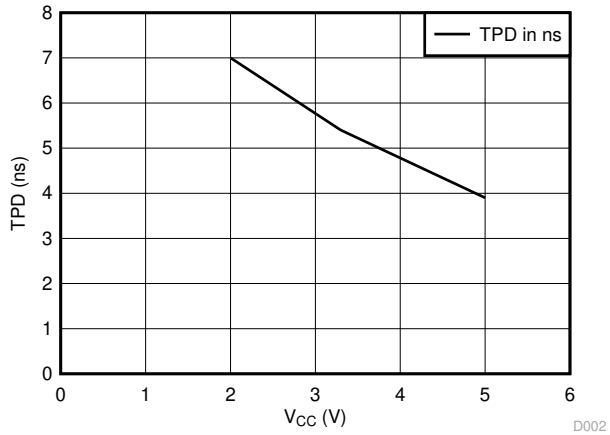

図 5-2. TPD vs V_{CC}

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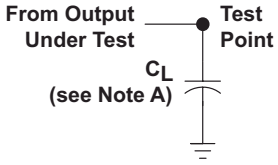
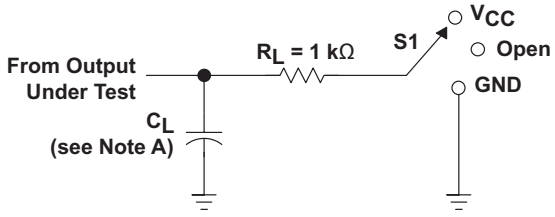
6 Parameter Measurement Information

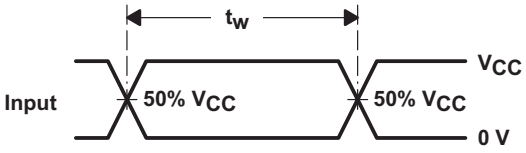


LOAD CIRCUIT FOR
TOTEM-POLE OUTPUTS

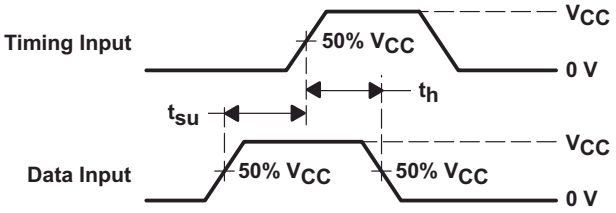


LOAD CIRCUIT FOR
3-STATE AND OPEN-DRAIN OUTPUTS

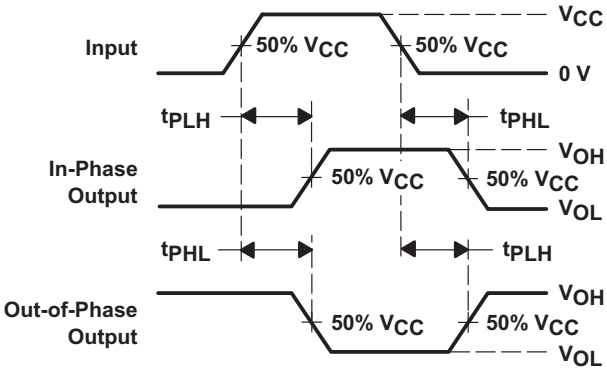
TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	V_{CC}
t_{PHZ}/t_{PZH}	GND
Open Drain	V_{CC}



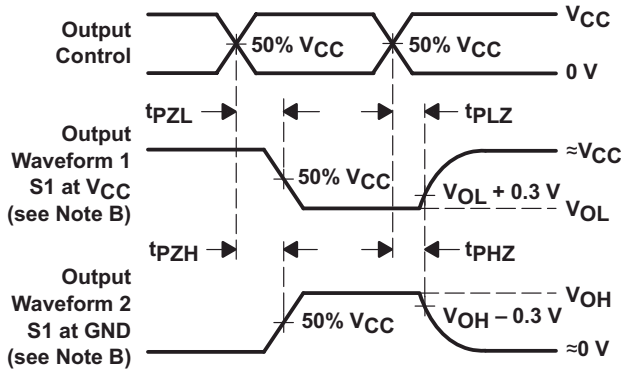
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low, except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 1 MHz, Z_O = 50 Ω, t_r ≤ 3 ns, t_f ≤ 3 ns.
D. The outputs are measured one at a time, with one input transition per measurement.
E. All parameters and waveforms are not applicable to all devices.

図 6-1. Load Circuit and Voltage Waveforms

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7 Detailed Description

7.1 Overview

The SN74AHC1G32 device is a single 2-input positive OR gate with low drive that produces slow rise and fall times. This reduces ringing on the output signal. The device also has Schmitt-trigger action that will allow for slower or noisier inputs. The input signals are high impedance when V_{CC} = 0 V.

7.2 Functional Block Diagram

7.3 Feature Description

- Wide operating voltage
  - Operates from 2 V to 5.5 V
- Allows down voltage translation
  - Accepts input voltages to 5.5 V

7.4 Device Functional Modes

表 7-1 shows the functional modes of the SN74AHC1G32 device.

表 7-1. Function Table

INPUTS(1)		OUTPUT(2)
A	B	Y
H	X	H
X	H	H
L	L	L

(1) H = High Voltage Level, L = Low Voltage Level, X = Don't Care
(2) H = Driving High, L = Driving Low, Z = High Impedance State

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8 Application and Implementation

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8.1 Application Information

The SN74AHC1G32 is a low-drive CMOS device that can be used for a multitude of bus-interface type applications where output ringing is a concern. The low drive and slow edge rates will minimize overshoot and undershoot on the outputs. The inputs can except voltages to 5.5 V at any valid V_{CC} making it ideal for down translation.

8.2 Typical Application

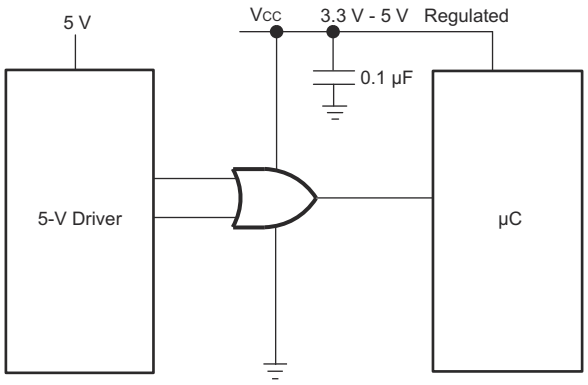

図 8-1. Specific Application Schematic

8.2.1 Design Requirements

This device uses CMOS technology and has balanced output drive. Take care to avoid bus contention because it can drive currents that would exceed maximum limits. The high drive will also create fast edges into light loads so routing and load conditions should be considered to prevent ringing.

8.2.2 Detailed Design Procedure

- Recommended input conditions
  - Specified high and low levels. See (V_{IH} and V_{IL}) in the *セクション 5.3* table.
  - Inputs are overvoltage tolerant allowing them to go as high as 5.5 V at any valid V_{CC}
- Recommended output conditions
  - Load currents should not exceed 25 mA per output and 50 mA total for the part
  - Outputs should not be pulled above V_{CC}

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8.2.3 Application Curve

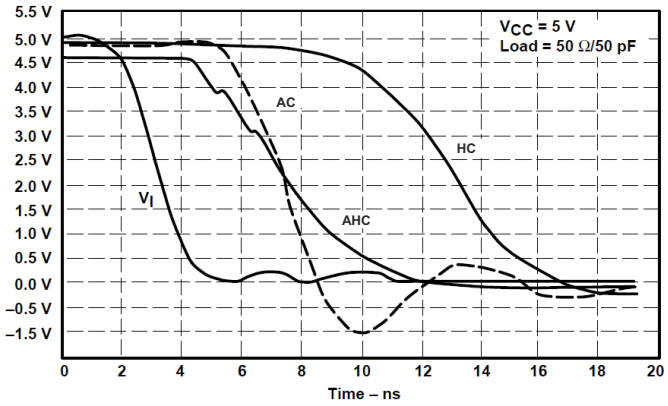

図 8-2. Switching Characteristics Comparison

8.3 Power Supply Recommendations

The power supply can be any voltage between the MIN and MAX supply voltage rating located in the *セクション 5.3* table.

Each V_{CC} pin should have a good bypass capacitor to prevent power disturbance. For devices with a single supply, 0.1 µf is recommended; if there are multiple V_{CC} pins, then 0.01 µf or 0.022 µf is recommended for each power pin. It is acceptable to parallel multiple bypass caps to reject different frequencies of noise. A 0.1 µf and a 1 µf are commonly used in parallel. The bypass capacitor should be installed as close to the power pin as possible for best results.

8.4 Layout

8.4.1 Layout Guidelines

When using multiple-bit logic devices, inputs should never float.

In many cases, functions or parts of functions of digital logic devices are unused, for example, when only two inputs of a triple-input AND gate are used or only 3 of the 4 buffer gates are used. Such input pins should not be left unconnected because the undefined voltages at the outside connections result in undefined operational states. 図 8-3 specifies the rules that must be observed under all circumstances. All unused inputs of digital logic devices must be connected to a high or low bias to prevent them from floating. The logic level that should be applied to any particular unused input depends on the function of the device. Generally they will be tied to GND or V_{CC}, whichever makes more sense or is most convenient. It is generally acceptable to float outputs, unless the part is a transceiver. If the transceiver has an output enable pin, it will disable the output section of the part when asserted. This will not disable the input section of the I/Os, so they cannot float when disabled.

8.4.2 Layout Example

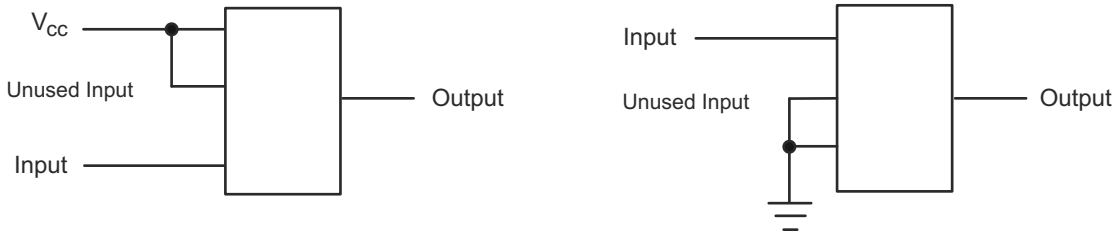

図 8-3. Layout Diagram

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9 Device and Documentation Support

9.1 Documentation Support (Analog)

9.1.1 Related Links

The table below lists quick access links. Categories include technical documents, support and community resources, tools and software, and quick access to sample or buy.

表 9-1. Related Links

PARTS	PRODUCT FOLDER	SAMPLE & BUY	TECHNICAL DOCUMENTS	TOOLS & SOFTWARE	SUPPORT & COMMUNITY
SN74AHC1G32	Click here	Click here	Click here	Click here	Click here

9.2 ドキュメントの更新通知を受け取る方法

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9.6 用語集

テキサス・インスツルメンツ用語集　　この用語集には、用語や略語の一覧および定義が記載されています。

10 Revision History

資料番号末尾の英字は改訂を表しています。その改訂履歴は英語版に準じています。

Changes from Revision P (February 2017) to Revision Q (April 2024)	Page
• 最新のデータシート規格を反映するように、文書全体にわたって採番方式、書式、表、図、相互参照を更新	1
• Updated RθJA values: DBV = 231.3 to 278, DCK = 287.6 to 293.4; Updated DBV and DCK packages for RθJC(top), RθJB, ΨJT, ΨJB, and RθJC(bot), all values in °C/W	5

Changes from Revision O (July 2014) to Revision P (February 2017)	Page
• Changed *Handling Ratings* table to *ESD Ratings* table	4
• Added MAX values for T_A = 25°C in both *Switching Characteristics* tables.	5

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11 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

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PACKAGING INFORMATION

Orderable part number	Status (1)	Material type (2)	Package | Pins	Package qty | Carrier	RoHS (3)	Lead finish/ Ball material (4)	MSL rating/ Peak reflow (5)	Op temp (°C)	Part marking (6)
SN74AHC1G32DBVR	Active	Production	SOT-23 (DBV) | 5	3000 | LARGE T&R	Yes	SN	Level-1-260C-UNLIM	-40 to 125	(39CH, 3C3F, A323, A32G, A32J, A 32L, A32S)
SN74AHC1G32DBVR.A	Active	Production	SOT-23 (DBV) | 5	3000 | LARGE T&R	Yes	SN	Level-1-260C-UNLIM	-40 to 125	(39CH, 3C3F, A323, A32G, A32J, A 32L, A32S)
SN74AHC1G32DBVRE4	Active	Production	SOT-23 (DBV) | 5	3000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	A32G
SN74AHC1G32DBVRG4	Active	Production	SOT-23 (DBV) | 5	3000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	A32G
SN74AHC1G32DBVRG4.A	Active	Production	SOT-23 (DBV) | 5	3000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	A32G
SN74AHC1G32DBVT	Obsolete	Production	SOT-23 (DBV) | 5	-	-	Call TI	Call TI	-40 to 125	(A323, A32G, A32J, A32S)
SN74AHC1G32DBVTG4	Obsolete	Production	SOT-23 (DBV) | 5	-	-	Call TI	Call TI	-40 to 125	A32G
SN74AHC1G32DCK3	Last Time Buy	Production	SC70 (DCK) | 5	3000 | LARGE T&R	Yes	SNBI	Level-1-260C-UNLIM	-40 to 85	AGY
SN74AHC1G32DCK3.A	Last Time Buy	Production	SC70 (DCK) | 5	3000 | LARGE T&R	Yes	SNBI	Level-1-260C-UNLIM	-40 to 85	AGY
SN74AHC1G32DCKR	Active	Production	SC70 (DCK) | 5	3000 | LARGE T&R	Yes	SN	Level-1-260C-UNLIM	-40 to 125	(1RA, AG3, AGG, AG J, AGL, AGS)
SN74AHC1G32DCKR.A	Active	Production	SC70 (DCK) | 5	3000 | LARGE T&R	Yes	SN	Level-1-260C-UNLIM	-40 to 125	(1RA, AG3, AGG, AG J, AGL, AGS)
SN74AHC1G32DCKRE4	Active	Production	SC70 (DCK) | 5	3000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	AG3
SN74AHC1G32DCKRG4	Active	Production	SC70 (DCK) | 5	3000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	AG3
SN74AHC1G32DCKRG4.A	Active	Production	SC70 (DCK) | 5	3000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	AG3
SN74AHC1G32DCKTE4	Active	Production	SC70 (DCK) | 5	250 | SMALL T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	AG3
SN74AHC1G32DCKTG4	Active	Production	SC70 (DCK) | 5	250 | SMALL T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	AG3
SN74AHC1G32DCKTG4.A	Active	Production	SC70 (DCK) | 5	250 | SMALL T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	AG3
SN74AHC1G32DRLR	Active	Production	SOT-5X3 (DRL) | 5	4000 | LARGE T&R	Yes	NIPDAU | NIPDAUAG	Level-1-260C-UNLIM	-40 to 125	(AGB, AGS)
SN74AHC1G32DRLR.A	Active	Production	SOT-5X3 (DRL) | 5	4000 | LARGE T&R	Yes	NIPDAUAG	Level-1-260C-UNLIM	-40 to 125	(AGB, AGS)
SN74AHC1G32DRLRG4	Active	Production	SOT-5X3 (DRL) | 5	4000 | LARGE T&R	Yes	NIPDAUAG	Level-1-260C-UNLIM	-40 to 125	(AGB, AGS)

(1) **Status:** For more details on status, see our product life cycle.

(2) **Material type:** When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

(3) **RoHS values:** Yes, No, RoHS Exempt. See the TI RoHS Statement for additional information and value definition.

(4) **Lead finish/Ball material:** Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

(5) **MSL rating/Peak reflow:** The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

(6) **Part marking:** There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

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In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

OTHER QUALIFIED VERSIONS OF SN74AHC1G32 :

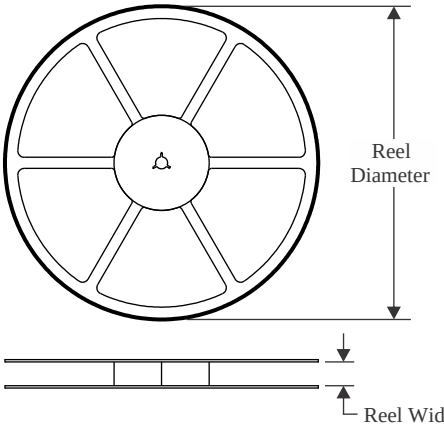
- Automotive : SN74AHC1G32-Q1

NOTE: Qualified Version Definitions:

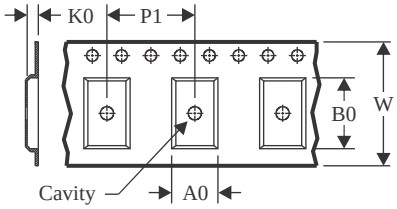
- Automotive - Q100 devices qualified for high-reliability automotive applications targeting zero defects

TAPE AND REEL INFORMATION

REEL DIMENSIONS

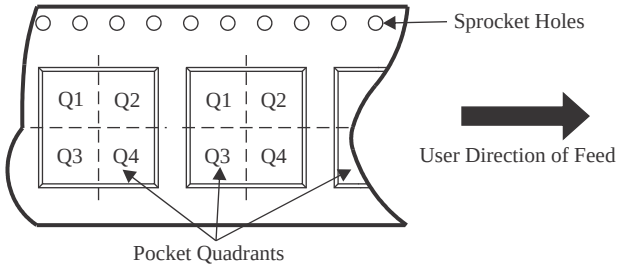


TAPE DIMENSIONS



A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

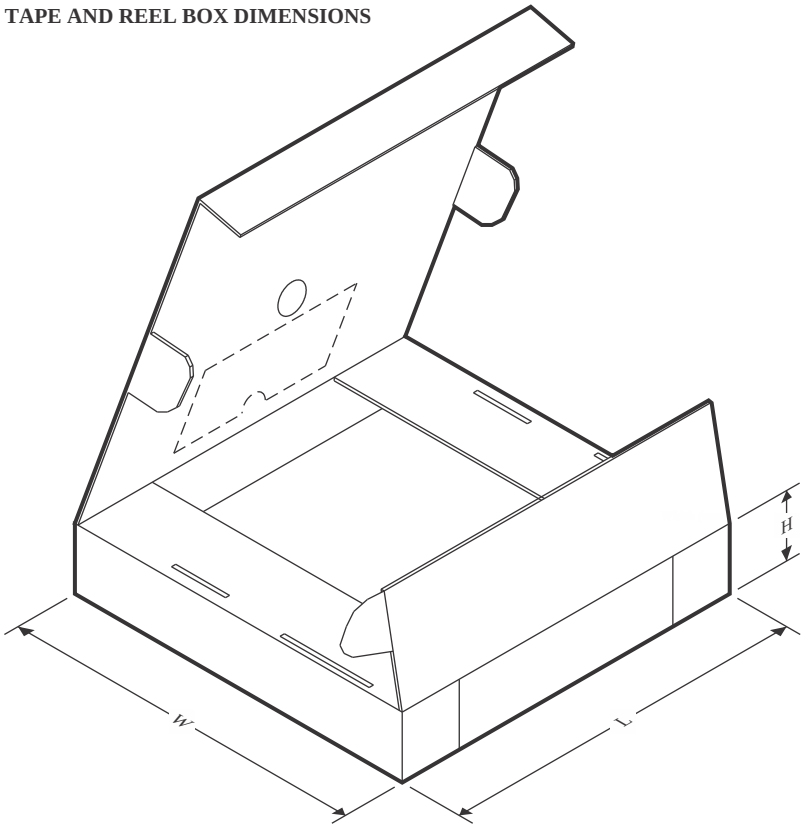
QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN74AHC1G32DBVR	SOT-23	DBV	5	3000	180.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
SN74AHC1G32DBVR	SOT-23	DBV	5	3000	180.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
SN74AHC1G32DBVRG4	SOT-23	DBV	5	3000	178.0	9.0	3.23	3.17	1.37	4.0	8.0	Q3
SN74AHC1G32DCKR	SC70	DCK	5	3000	180.0	8.4	2.3	2.5	1.2	4.0	8.0	Q3
SN74AHC1G32DCKRG4	SC70	DCK	5	3000	178.0	9.2	2.4	2.4	1.22	4.0	8.0	Q3
SN74AHC1G32DCKTG4	SC70	DCK	5	250	178.0	9.2	2.4	2.4	1.22	4.0	8.0	Q3
SN74AHC1G32DRLR	SOT-5X3	DRL	5	4000	180.0	8.4	1.98	1.78	0.69	4.0	8.0	Q3

TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

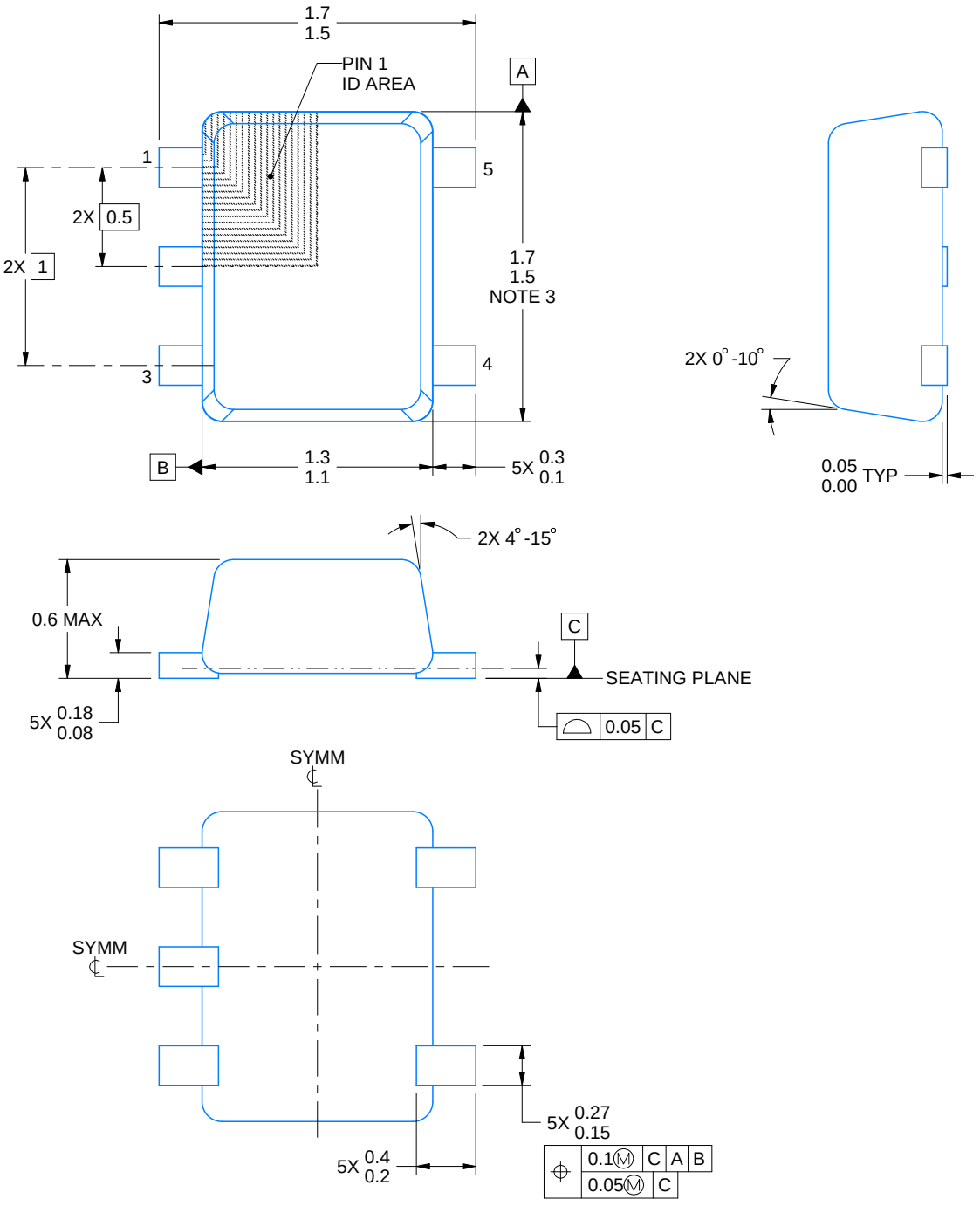
Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN74AHC1G32DBVR	SOT-23	DBV	5	3000	210.0	185.0	35.0
SN74AHC1G32DBVR	SOT-23	DBV	5	3000	210.0	185.0	35.0
SN74AHC1G32DBVRG4	SOT-23	DBV	5	3000	180.0	180.0	18.0
SN74AHC1G32DCKR	SC70	DCK	5	3000	210.0	185.0	35.0
SN74AHC1G32DCKRG4	SC70	DCK	5	3000	180.0	180.0	18.0
SN74AHC1G32DCKTG4	SC70	DCK	5	250	180.0	180.0	18.0
SN74AHC1G32DRLR	SOT-5X3	DRL	5	4000	202.0	201.0	28.0

PACKAGE OUTLINE

DRL0005A

SOT - 0.6 mm max height

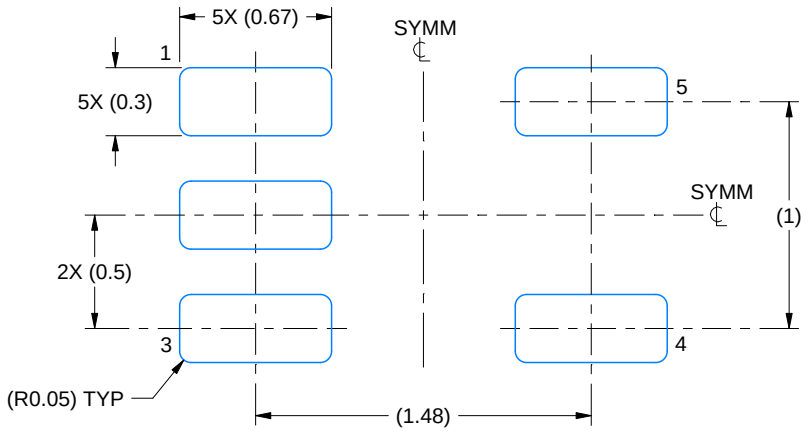
PLASTIC SMALL OUTLINE



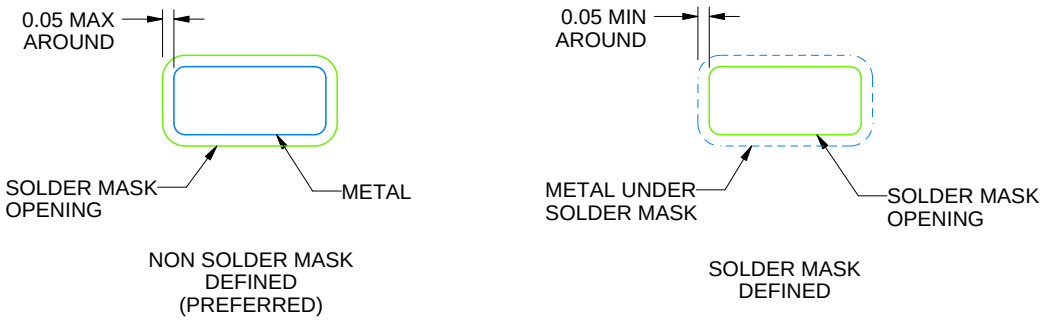
4220753/E 11/2024

NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.
4. Reference JEDEC registration MO-293 Variation UAAD-1



LAND PATTERN EXAMPLE
SCALE:30X

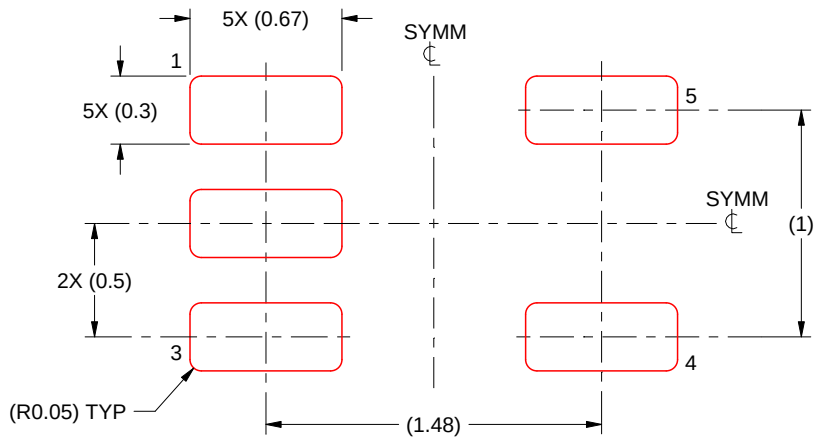


SOLDERMASK DETAILS

4220753/E 11/2024

NOTES: (continued)

5. Publication IPC-7351 may have alternate designs.
6. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SOLDER PASTE EXAMPLE
BASED ON 0.1 mm THICK STENCIL
SCALE:30X

4220753/E 11/2024

NOTES: (continued)

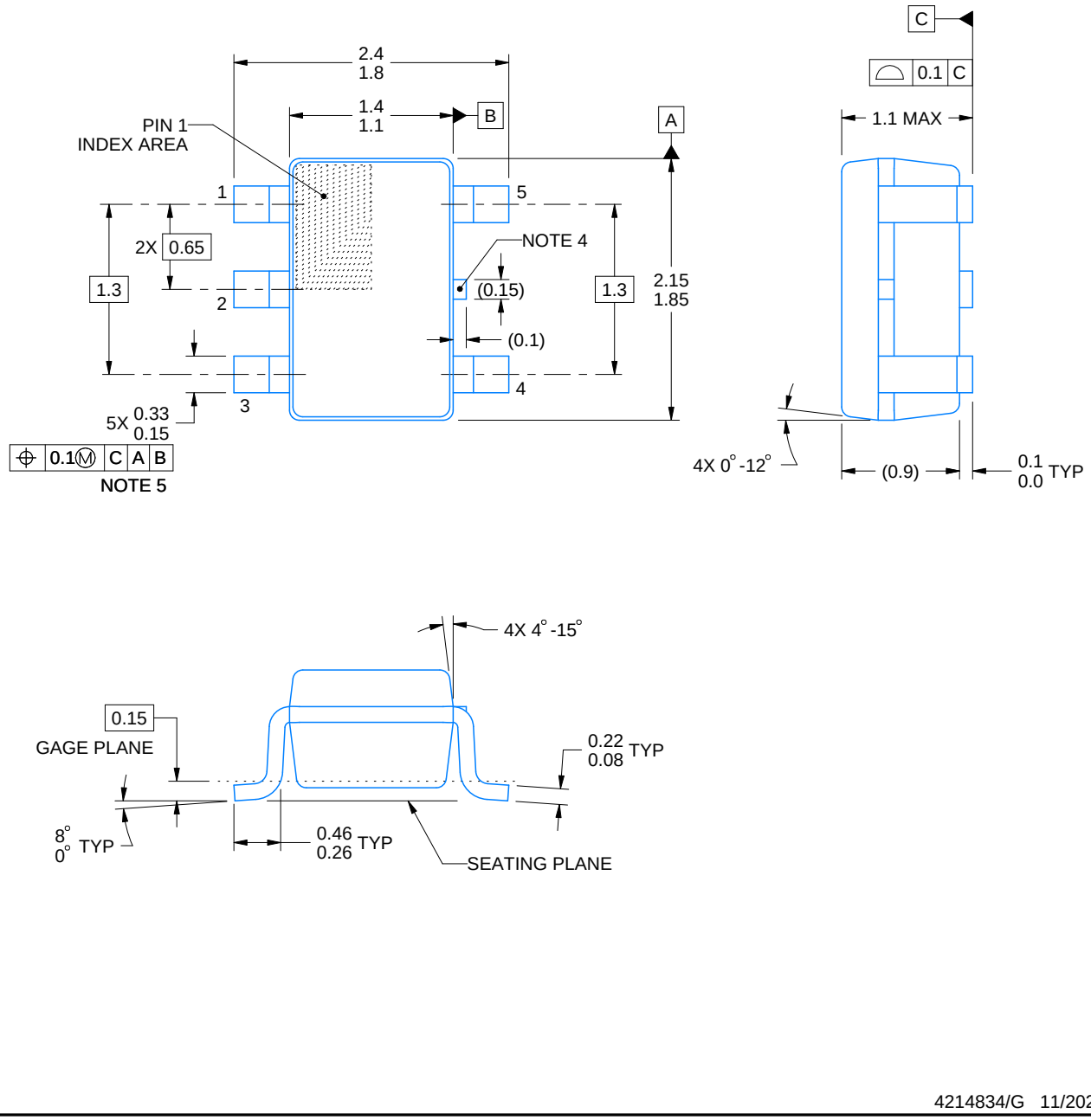
7. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
8. Board assembly site may have different recommendations for stencil design.

PACKAGE OUTLINE

DCK0005A

SOT - 1.1 max height

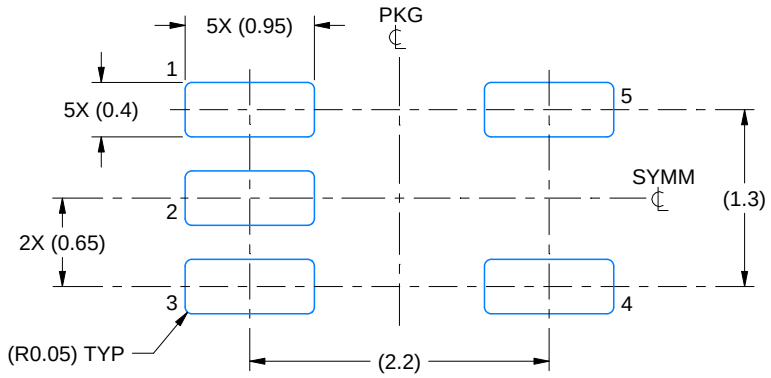
SMALL OUTLINE TRANSISTOR



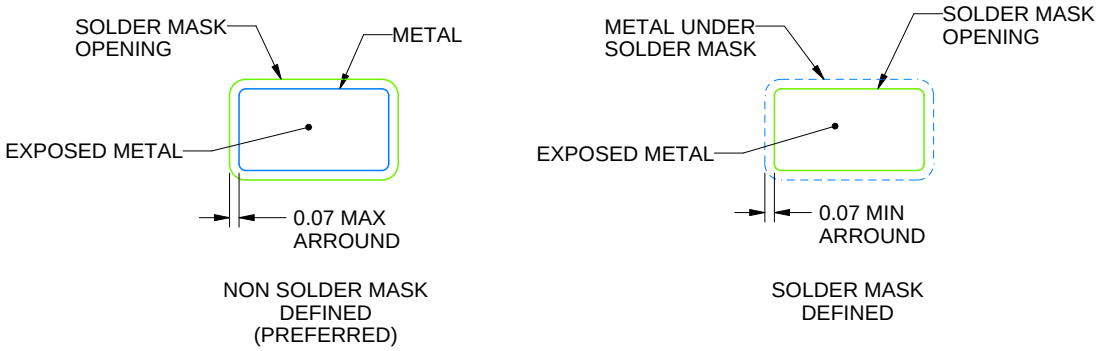
4214834/G 11/2024

NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. Refernce JEDEC MO-203.
4. Support pin may differ or may not be present.
5. Lead width does not comply with JEDEC.
6. Body dimensions do not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.25mm per side



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE:18X

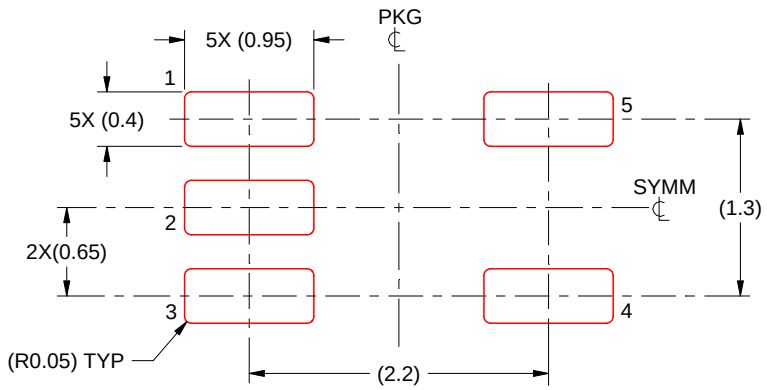


SOLDER MASK DETAILS

4214834/G 11/2024

NOTES: (continued)

7. Publication IPC-7351 may have alternate designs.
8. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SOLDER PASTE EXAMPLE
BASED ON 0.125 THICK STENCIL
SCALE:18X

4214834/G 11/2024

NOTES: (continued)

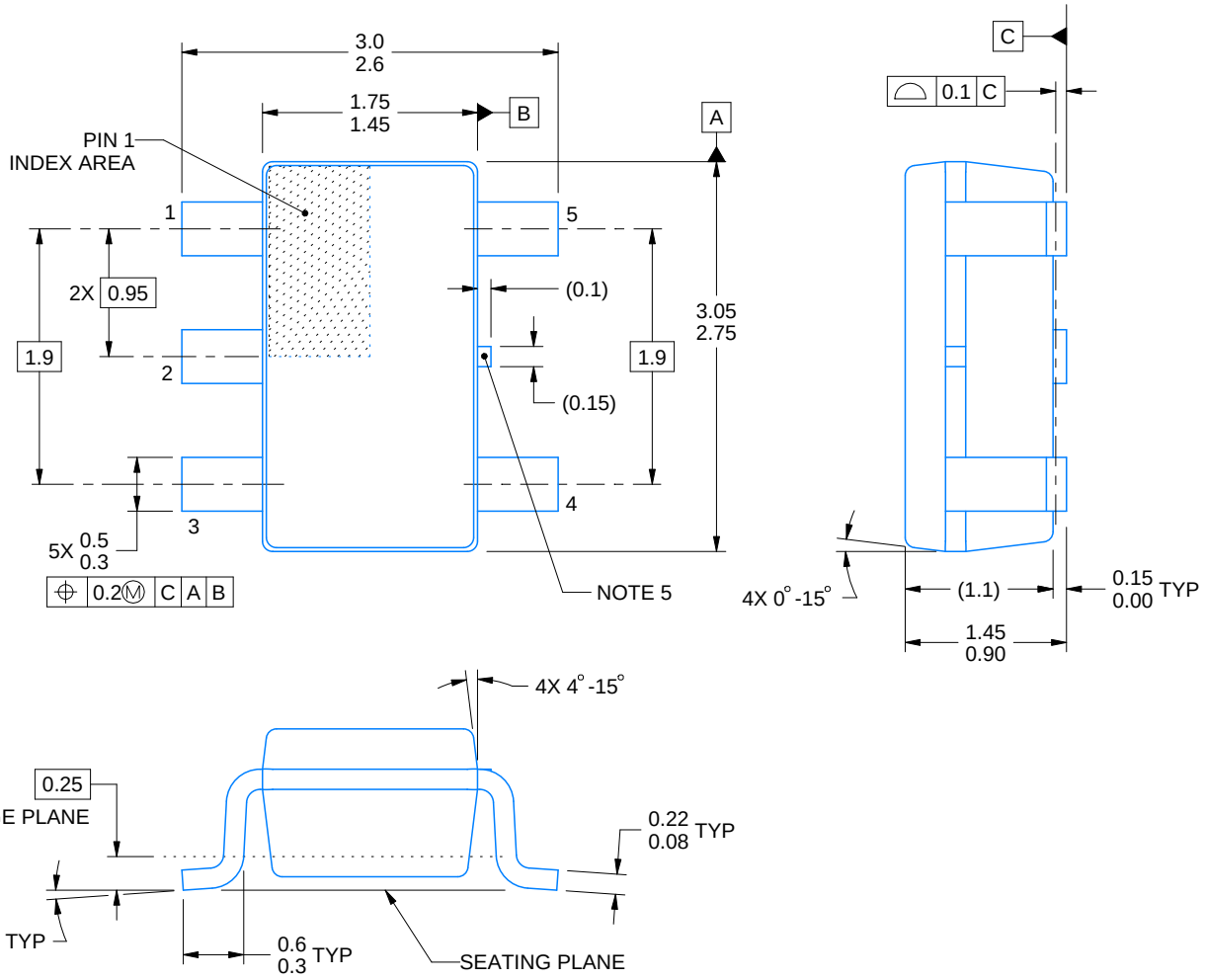
9. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
10. Board assembly site may have different recommendations for stencil design.

PACKAGE OUTLINE

DBV0005A

SOT-23 - 1.45 mm max height

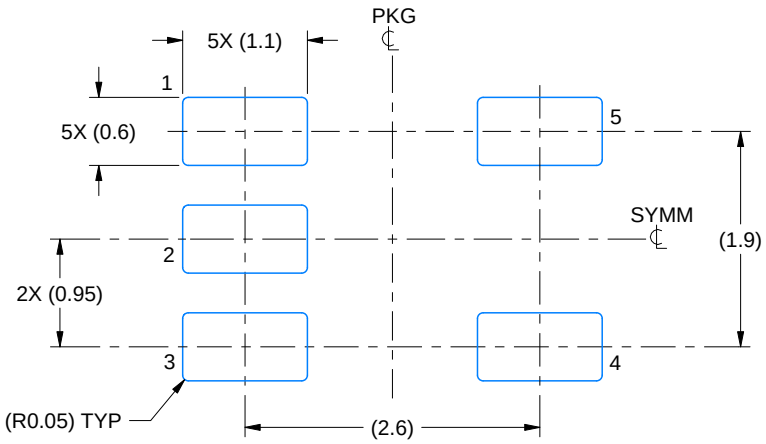
SMALL OUTLINE TRANSISTOR



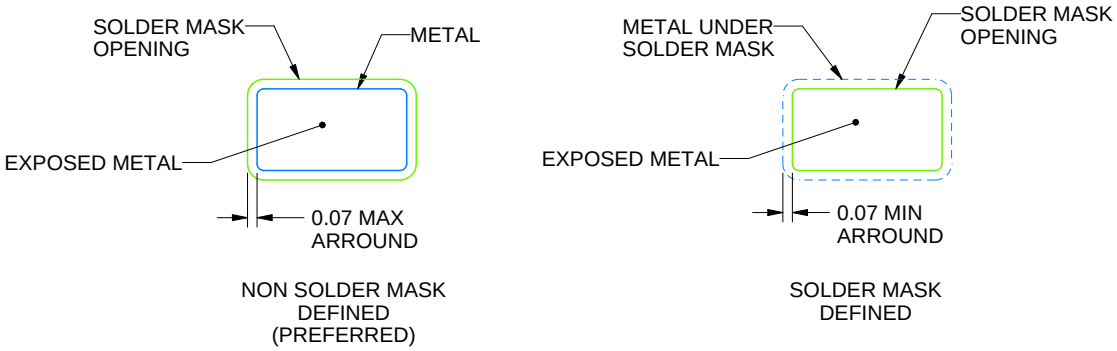
4214839/K 08/2024

NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. Refernce JEDEC MO-178.
4. Body dimensions do not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.25 mm per side.
5. Support pin may differ or may not be present.



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE:15X

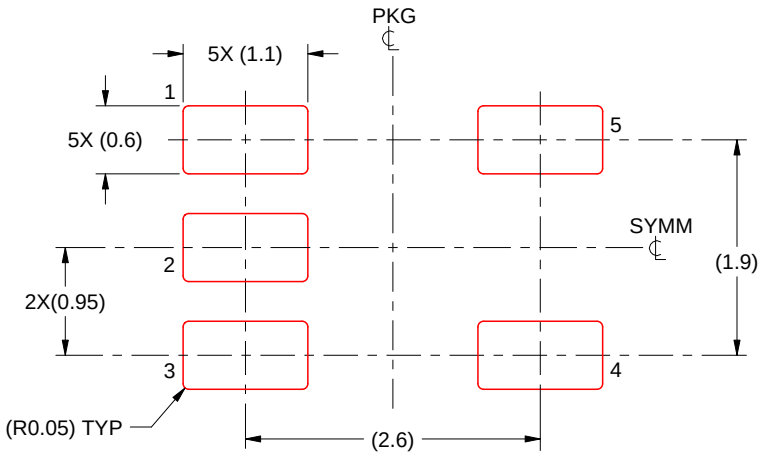


SOLDER MASK DETAILS

4214839/K 08/2024

NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE:15X

4214839/K 08/2024

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

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